

IRF 240
MOS-FET N-Channel enhanced

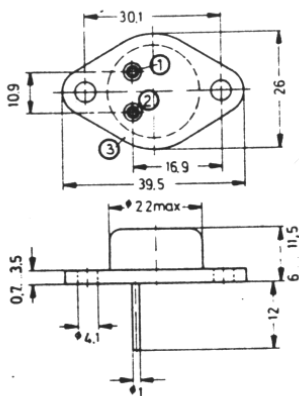
Text: V-MOS, L
Case: H9/a\$
Prod.:

Inr: International Rectifier Corporation
Gen: Harris (General Electric) Semiconductor
Mot: Motorola GmbH
Fch: Fairchild Semiconductor GmbH
Sam: SAMSUNG Semiconductor Europe GmbH

UDS: 200V
UGS: $\pm 20V$
ID: 18A
IDM: 72A
Ptot: 125W@Tg: 25°C
RthG: 1°C/W
RthU: 30°C/W
Tj: 150°C

rds(on) typ: 0,14Ohm@UGS: 10V
IDtyp: 10A
Idss max: 0,25mA@UDS: max
rds(on) max: 0,18Ohm@UGS: 10V
Uth min: 2V@UDS: =UGSV ID: 250 μ A
Uth max: 4V@UDS: =UGSV ID: 250 μ A
gfs min: 6,7SmS@UDS: 50V ID: 10A
gfs typ: 10SmS@UDS: 50V ID: 10A
t_on max: 98ns
t_off max: 122ns
IGSS: $\pm 100nA$ @UGS: $\pm 20V$

M



H9

TO-3

Pin1: Source
Pin2: Gate
Pin3: Drain
Drain + Case connected